Session Program

2–4 Jun 2005

6th RD50 - Workshop on Radiation hard semiconductor devices for very high luminosity colliders

New Materials

Physicum campus, University of Helsinki, Finland, 0--E204

Thursday 2 June

16:00

New Materials

Session | **Location:** Helsinki, Finland, 0--E204

16:00–16:20 **Minimum ionizing particle detector based on p+n junction SiC diode**

Speaker
Francesco Moscatelli

Location
Helsinki, Finland, 0--E204

16:20–16:40

Properties of 12 micron thick epitaxial GaN irradiated up to 1e16 cm2 by 24 GeV protons

Speaker
Juozas Vaitkus

Location
Helsinki, Finland, 0--E204

16:40–17:00

I-V & CCE Characterisation of Proton Irradiated 12 Micron Epitaxial GaN Detectors

Speaker
James Grant

Location
Helsinki, Finland, 0--E204

17:00–17:20

COMPARISON OF SHALLOW DONOR FORMARION AND RADIATION DEFECT ELIMINATION IN HYDROGENATED PARTICLE DETECTORS MADE OF STANDARD AND DIFFUSION OXYGENATED SILICON

Speaker
Leonid Makarenko

Location
Helsinki, Finland, 0--E204

17:20–17:40

EVALUATION OF OXYGEN AND CARBON CONTENT IN STANDARD FLOAT ZONE SILICON DETECTORS

Speaker
Leonid Makarenko

Location
Helsinki, Finland, 0--E204

17:40